

a semiconductor substrate of a first conductivity type;  
a first region of a second conductivity type formed on and in direct contact with said semiconductor substrate;

*fig.14, 1*  
a second region of the second conductivity type formed at and near the surface of said first region;

*A3*  
a third region of the first conductivity type formed at and near the surface of said first region, and surrounding said second region;

a first electrode portion formed on the surface of said third region located between said first and second regions with an insulating film therebetween;

a second electrode portion connected to said second region;

a third electrode portion connected to said first region and spaced by a distance from said third region; and

a fourth region of the first conductivity type formed at and near the surface of said first region between said third electrode portion and said third region;

wherein, in an on state a depletion layer extends from said fourth region, and  
said depletion layer having a depth changing as a position moves in a direction crossing a direction of flow of the current.

Please amend claim 5 as follows:

*apply to the depletion layer the 4 regions*  
5. (Amended) The semiconductor device according to claim 1, wherein said fourth region comprises a plurality of discretely formed neighboring regions, and the neighboring fourth regions are spaced from each other by a distance allowing connection between depletion layers extending from the neighboring fourth regions, respectively, in the on state.